

< C band internally matched power GaAs FET >

MGFC40V3742

<u> 3.7 – 4.2 GHz BAND / 10W</u>

DESCRIPTION

The MGFC40V3742 is an internally impedance-matched GaAs power FET especially designed for use in 3.7 - 4.2 GHz band amplifiers. The hermetically sealed metal-ceramic package guarantees high reliability.

FEATURES

Class A operation

Internally matched to 50(ohm) systemHigh output power

- P1dB=10W (TYP.) @f=3.7 4.2GHz • High power gain
- GLP=11dB (TYP.) @f=3.7 4.2GHz • High power added efficiency
- P.A.E.=32% (TYP.) @f=3.7 4.2GHz • Low distortion [item -51]
- IM3=-45dBc (TYP.) @Po=29dBm S.C.L

APPLICATION

- item 01 : 3.7 4.2 GHz band power amplifier
- item 51 : 3.7 4.2 GHz band digital radio communication

• IG

RECOMMENDED BIAS CONDITIONS

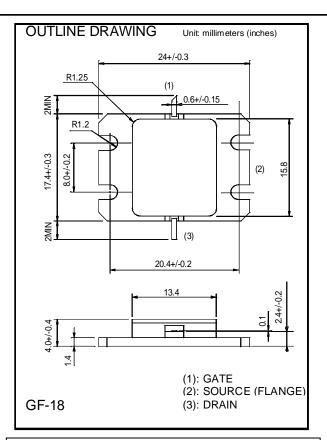
• VDS=10V • ID=2.4A • RG=50ohm Refer to Bias Procedure

Absolute maximum ratings (Ta=25°C)

Symbol	Parameter	Ratings	Unit				
VGDO	Gate to drain breakdown voltage	-15	V				
VGSO	Gate to source breakdown voltage	-15	V				
ID	Drain current	7.5	А				
IGR	Reverse gate current	-20	mA				
IGF	Forward gate current	42	mA				
PT *1	Total power dissipation	42.8	W				
Tch	Cannel temperature	175	°C				
Tstg	Storage temperature	-65 to +175	°C				
*1 . T- 0500							

*1 : Tc=25°C

Electrical characteristics (Ta=25°C)



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Symbol	Parameter	Test conditions	Limits		Unit	
			Min.	Тур.	Max.	
IDSS	Saturated drain current	VDS=3V,VGS=0V	-	4.5	6	А
gm	Transconductance	VDS=3V,ID=2.2A	-	2	-	S
VGS(off)	Gate to source cut-off voltage	VDS=3V,ID=40mA	-2	-3	-4	V
P1dB	Output power at 1dB gain compression	VDS=10V,ID(RF off)=2.4A	39.5	40.5	-	dBm
GLP	Linear Power Gain	f=3.7 – 4.2GHz	9	11	-	dB
ID	Drain current		-	2.4	-	А
P.A.E.	Power added efficiency		-	32	-	%
IM3 *2	3rd order IM distortion	7	-42	-45	-	dBc
Rth(ch-c) *3	Thermal resistance	delta Vf method	-	-	3.5	°C/W

*2 :item -51 ,2 tone test,Po=29dBm Single Carrier Level ,f=4.2GHz,delta f=10MHz

*3 :Channel-case

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